Thyristor Semiconductor Device - Page 1 of 1



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Inclosure Material:
Metal
Overall Length:
2.637 inches
Overall Diameter:
1.031 inches
Mounting Facility Quantity:
1
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
То-83
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Overall Width Across Flats:
Between 1.031 inches and 1.063 inches
Thread Size:
0.500 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
1500.0 repetitive peak reverse voltage and 1800.0 nonrepetitive peak reverse voltage
Current Rating Per Characteristic:
10.00 milliamperes forward current, total rms and 10.00 milliamperes forward current, average nanoamperes
Power Rating Per Characteristic:
16.0 watts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius junction
Thread Series Designator:
Unf
Terminal Type And Quantity:
2 tab, solder lug and 1 threaded stud
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig:
A110a0
Fiig: